

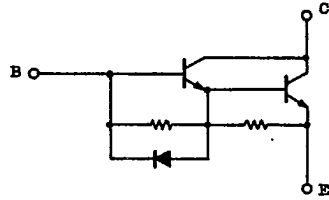
9097250 TOSHIBA (DISCRETE/OPTO)

90D 16219 DT-33-35

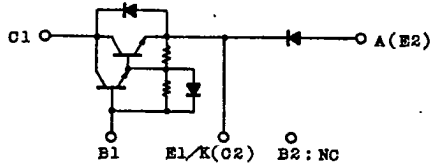


SEMICONDUCTOR
TECHNICAL DATA

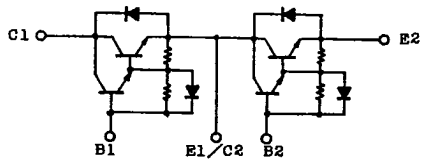
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- MG30G1JL1
- MG30G2CL3
- MG30G2DL1
- MG30G6EL1



MG30G1BL3

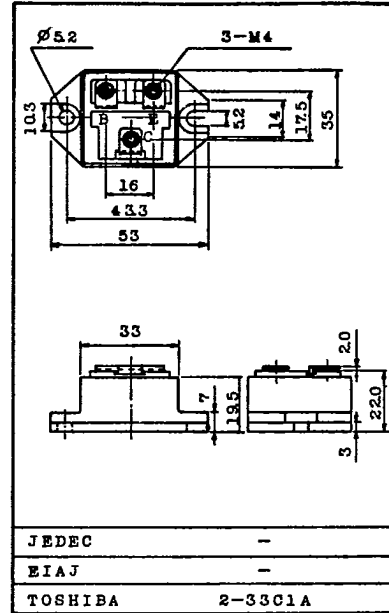


MG30G1JL1

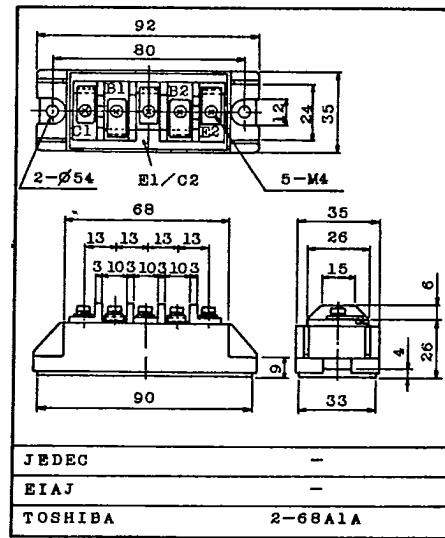


MG30G2CL3

Unit in mm



Weight : 86g



Weight : 210g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

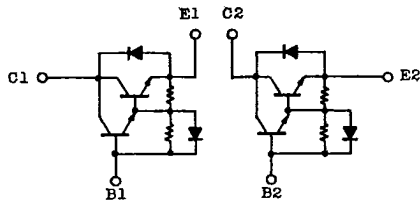
90D 16220 DT-33-35



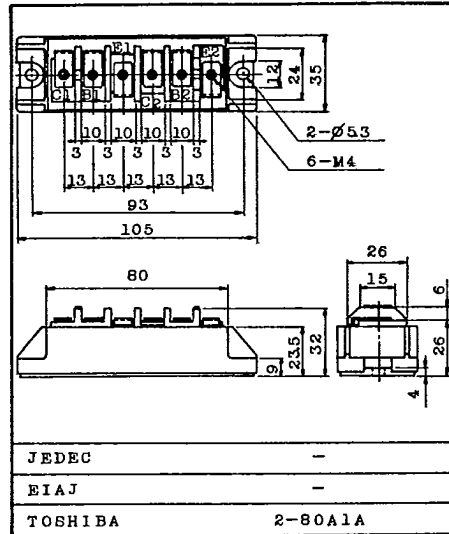
SEMICONDUCTOR
TECHNICAL DATA

- MG30G1BL3
- MG30G1JL1
- MG30G2CL3
- MG30G2DL1
- MG30G6EL1

MG30G2DL1

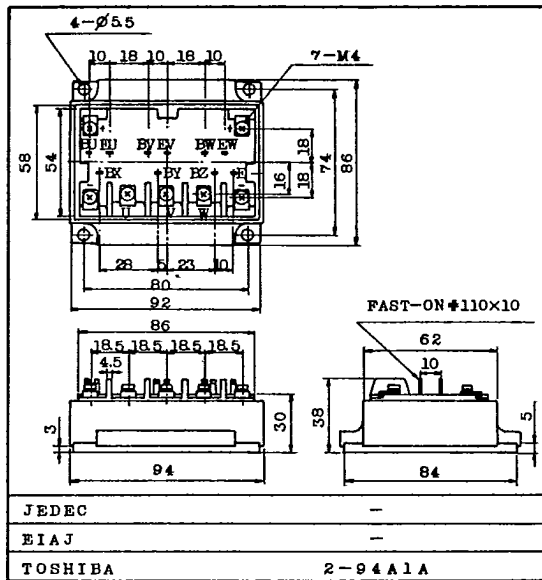
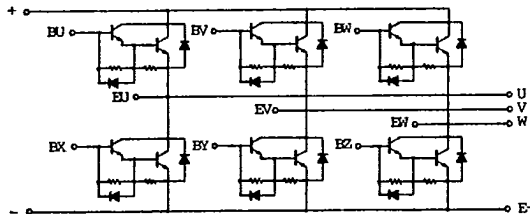


Unit in mm



Weight : 245g

MG30G6EL1



Weight : 600g

TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)



SEMICONDUCTOR

TECHNICAL DATA

90D 16221 DT-33-35

 MG30G1BL3
 MG30G1JL1
 MG30G2CL3
 MG30G2DL1
 MG30G6EL1

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		VCBO	600	V
Collector-Emitter Sustaining Voltage		VCEX(SUS)	600	V
Collector-Emitter Sustaining Voltage		VCEO(SUS)	450	V
Emitter-Base Voltage		VEBO	6	V
Collector Current	DC	IC	30	A
	lms	ICP	60	A
Forward Current	DC	IF	30	A
	lms	IFM	60	A
Base Current		IB	2	A
Collector Power Dissipation (Tc=25°C)		PC	250	W
Junction Temperature		Tj	150	°C
Storage Temperature Range		Tstg	-40 ~ 125	°C
Isolating Voltage		VIsol	2500 (AC 1 Minute)	V
Screw Torque (Terminal/Mounting)		-	20/30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	VCB=600V, IE=0	-	-	1.0	mA
Emitter Cut-off Current		IEBO	VEB=6V, IC=0	-	-	200	mA
Collector-Emitter Sustaining Voltage		VCEX(SUS)	IC=0.5A, L=40mH	450	-	-	V
DC Current Gain		hFE	VCE=5V, IC=30A	100	-	-	
Collector-Emitter Saturation Voltage		VCE(sat)	IC=30A, IB=0.6A	-	-	2.0	V
Base-Emitter Saturation Voltage		VBE(sat)		-	-	2.5	V
Switching Time	Turn-on Time	ton		-	-	1.0	µs
	Storage Time	tstg		-	-	12	
	Fall Time	tf		-	-	2.0	
Forward Voltage		VF	IF=30A, IB=0	-	-	1.5	V
Reverse Recovery Time		trr	IF=30A, VBE=-3V di/dt=100A/µs	-	-	2.0	µs
Thermal Resistance		Rth(j-c)	Transistor	-	-	0.5	°C/W
			Diode	-	-	1.8	

TOSHIBA CORPORATION

GT1A2A

- 227 -

9097250 TOSHIBA (DISCRETE/OPTO)

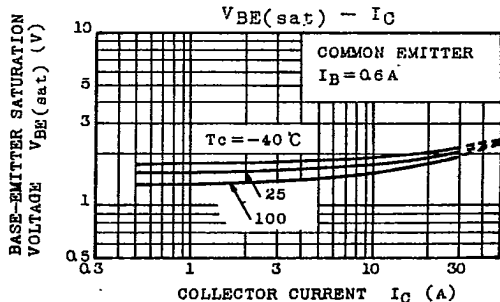
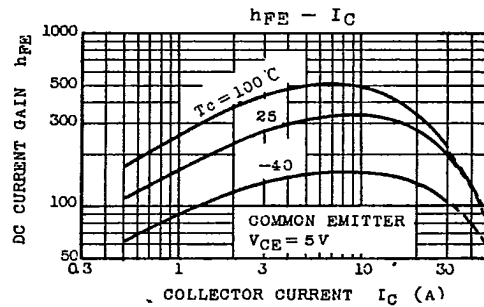
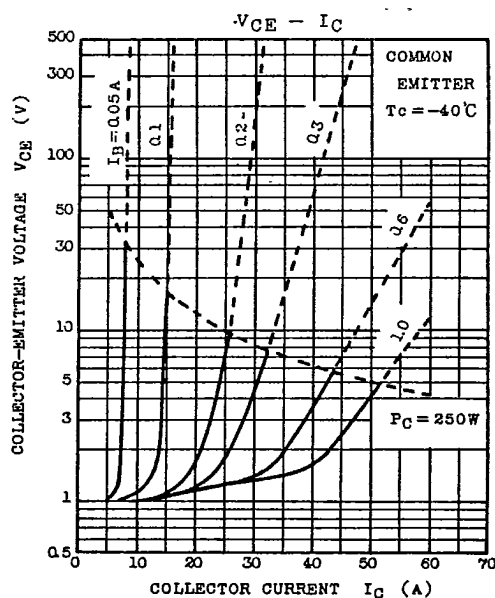
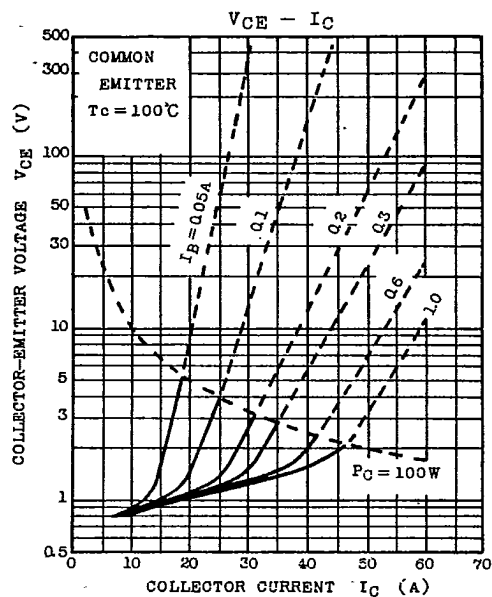
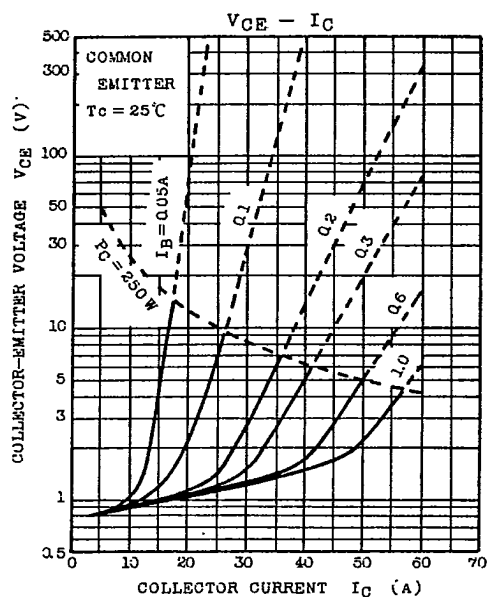
90D 16222 DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

- MG 3 0 G 1 B L 3
- MG 3 0 G 1 J L 1
- MG 3 0 G 2 C L 3
- MG 3 0 G 2 D L 1
- MG 3 0 G 6 E L 1



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16223 DT-33-35

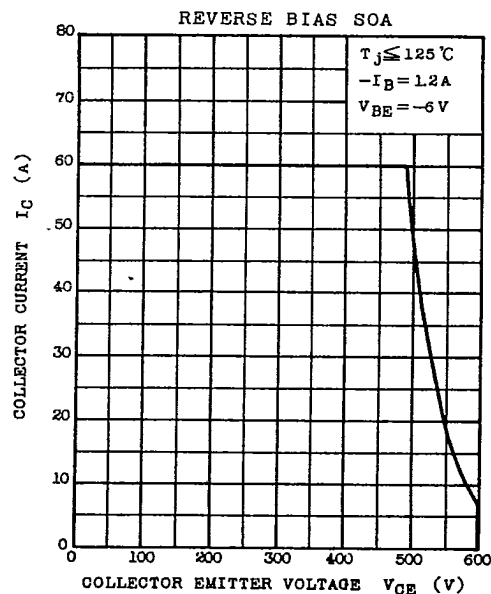
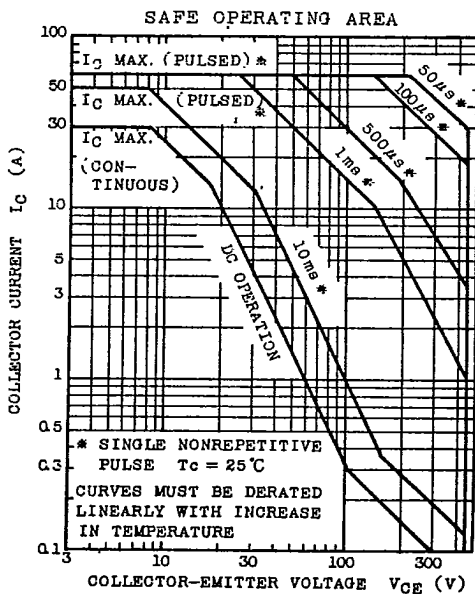
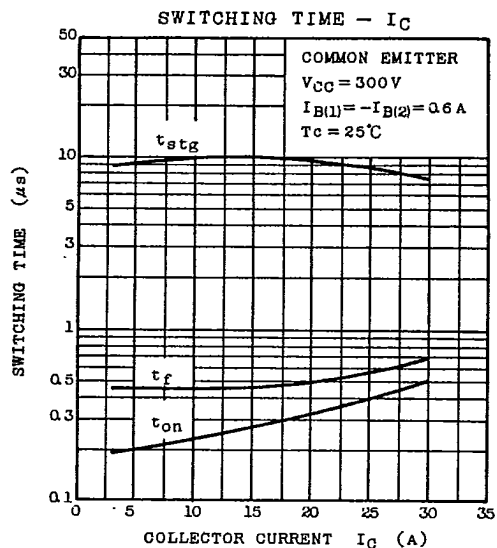
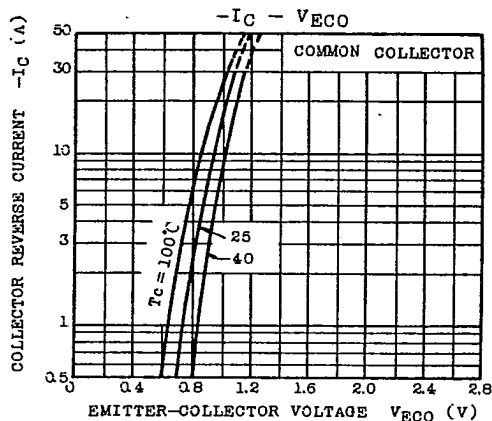


SEMICONDUCTOR

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TECHNICAL DATA

- MG 30 G 1 B L 3
- MG 30 G 1 J L 1
- MG 30 G 2 C L 3
- MG 30 G 2 D L 1
- MG 30 G 6 E L 1



TOSHIBA CORPORATION

GT1A2

9097250 TOSHIBA (DISCRETE/OPTO)

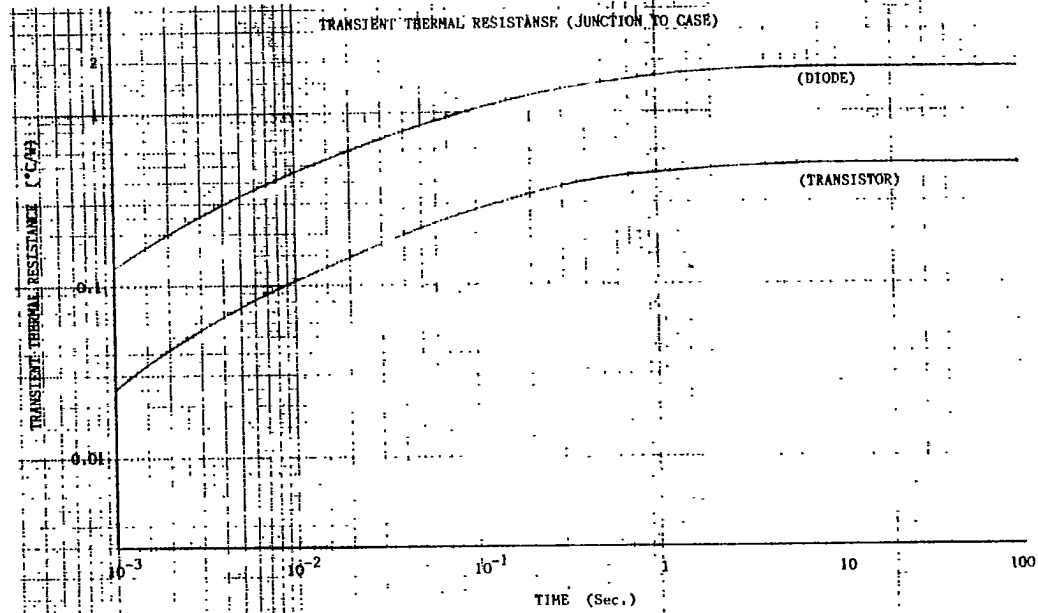
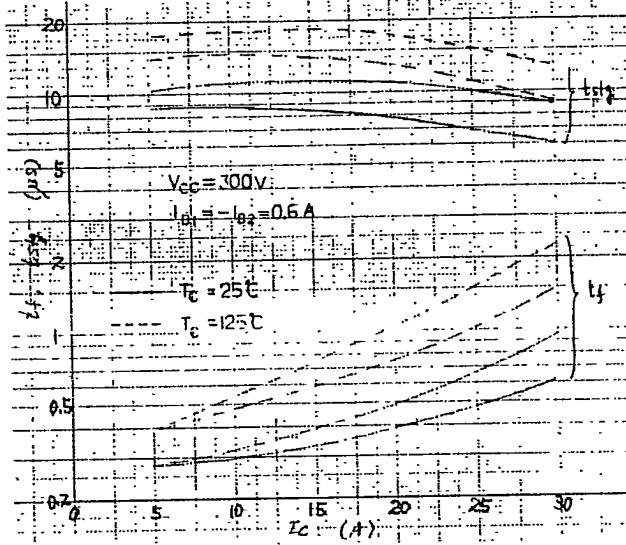
90D 16224

DT-33-35



SEMICONDUCTOR TECHNICAL DATA

- MG30G1BL3
- MG30G1JL1
- MG30G2CL3
- MG30G2DL1
- MG30G6EL1



TOSHIBA CORPORATION

GT1A2A

9097250 TOSHIBA (DISCRETE/OPTO)

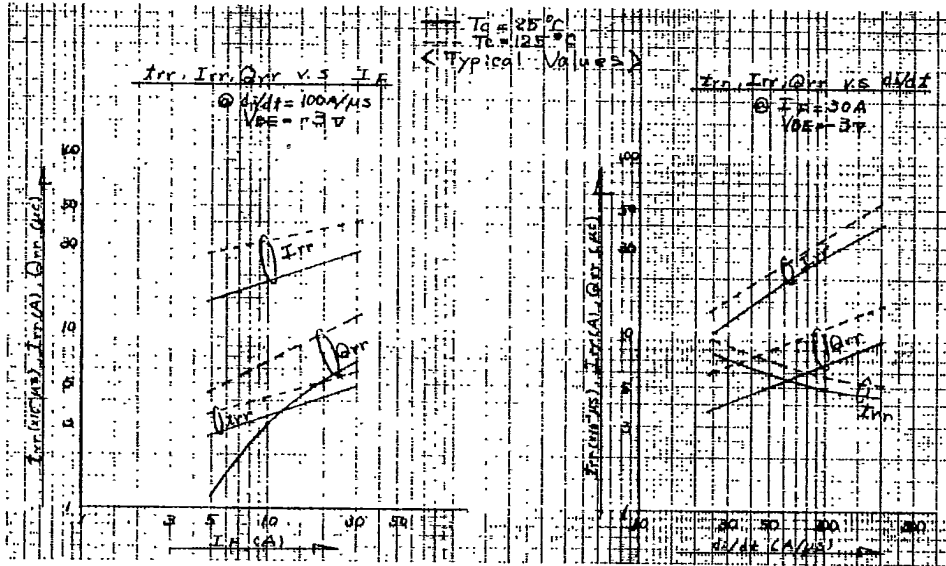
90D 16225 DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

- MG30G1BL3
- MG30G1JL1
- MG30G2CL3
- MG30G2DL1
- MG30G6EL1



TOSHIBA CORPORATION

GT1A2A